

## Ascatron SiC Process Tools

Ascatron SiC epi and device manufacturing is located at the Electrum Laboratory outside Stockholm. The clean-room has a total area of 1300 m<sup>2</sup> and provides the access to all equipment needed for processing of 100 mm diameter SiC wafers. The SiC process line has a capacity of 1000 wafers per year.

Process	Type	Parameters	Tools	Cap
<b>Epitaxy</b>	Hot-wall CVD	n/p 4H-, 6H, 3C-SiC n-doping 10 <sup>14</sup> -10 <sup>19</sup> cm <sup>-3</sup> p-doping 10 <sup>14</sup> -10 <sup>20</sup> cm <sup>-3</sup> Thickness up to 180 μm	2 Aixtron VP508GFR	S
<b>Doping</b>	Ion Implanter	40-330keV - Al, B, N, P RT & 600 °C	Danfysik 1090*	S
<b>Furnace Processes</b>	Thermal Oxidations	Wet/Dry/N <sub>2</sub> O (900-1250°C)	Thermco 5200	B
	LPCVD	LTO, TEOS, Polysilicon	Bruce Furnace	B
	Annealing	1400-1800 °C in Ar	Centrotherm Activator 150	B
	RTP		Mattson 100 RTP	S
<b>Plasma Deposition</b>	PECVD	SiO <sub>2</sub> , Si <sub>3</sub> N <sub>4</sub>	Oxford Plasmalab 80 Applied Materials P5000	S S
<b>Plasma Etching</b>	RIE		Oxford Plasmalab 80 Oxford Plasmalab 100 Applied Materials P5000	S S S
		ICP	STS ICP DRIE Oxford ICP380	S S
	Microwave plasma ash	O <sub>2</sub>	TePla300	B
<b>Wet Etching</b>	Wet cleaning process	Acid and solvent based		B
<b>Metallisation</b>	Plasma sputter	Au, Ni, Al, Ag, TiW	KDF 844NT, MRC 643	B
	Ion-beam sputter	Au, Ni, Al, Ti	Commonwealth IBS	B
	Evaporation	Au	PAK600	B
<b>Lithography</b>	Contact	Alignment Accuracy ~1μm Minimum Features ~1.5 μm	Karl Suss MA8	S
	Stepper	Alignment Accur. ~ 0.3 μm Minimum Features ~ 1μm	ALS 2035 G-line	S
	Lift-off			B
<b>Metrology</b>	SEM		Zeiss Ultra 55, Hitachi S-3400N	S S
	Ellipsometer		Horiba Uvisel ER SENTECH instrum.	S S
	Surface Profiler		Tencor-P10, Dektak3ST	S S
	AFM		Veeco Dimension 3100	S
	Sheet Resistance	4-point probe	Four Dimension 280	S
	Inspection Microscope		Nikon, Olympus, Leitz	S
<b>Testing</b>	Automated Probing		Karl Suss PA 150 Electroglass	S B
		<b>Dicing</b>	High Speed Saw	Disco DFD640

Capacity of respective tool is marked as single wafer (S) and batch processing (B).

Equipment excluding epitaxy, RTP and LPCVD also compatible with 150 mm substrates.

\* Performed at Ion Technology Center, Ångström Laboratory in Uppsala